ABSTRACT

In a CMP process for polishing copper and a barrier metal formed on a substrate to form a buried copper interconnect, a polishing pad is subjected to dressing under a dressing pressure of $29g/cm^2$ so that the surface roughness of the polishing pad becomes 3μm to 5μm inclusive. Thereby, dishing of the copper interconnect can be reduced as compared with a known method without reducing the removal rate of the copper and barrier metal.